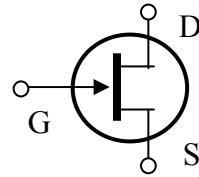


Guangdong Yuejing High Technology CO.,LTD.

N-Channel Junction FET

K596

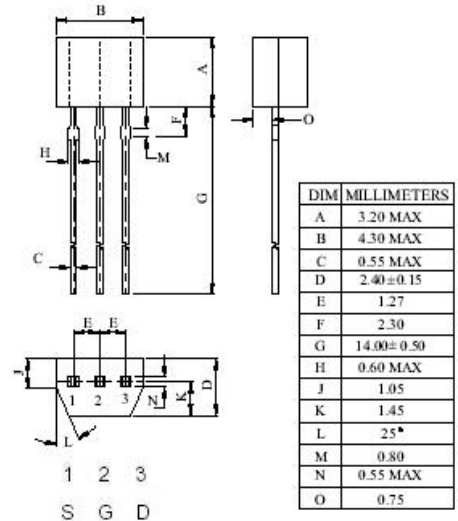
■■ APPLICATION: Capacitor Microphone application.



■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Drain-gate Voltage	V_{GD0}	-20	V
Drain Current	I_D	1	mA
Gate Current	I_G	10	mA
MAX.Drain Power	P_D	100	mW
Junction Temperature	T_J	125	°C
Storage Temperature Range	T_{stg}	- 55~125	°C

TO-92S



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	TEST CONDITION	RATING			UNIT
			MIN.	TYP.	MAX.	
Drain- source Current	I_{DSS}	$V_{DS}=5V, V_{GS}=0$	100		350	μA
Drain- source Breakdown Voltage	$V_{(BR)GD0}$	$I_G = -100\mu A, V_{GS} = 0$	-20			V
Gate-source Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 5 V, I_D = 1 \mu A$		-0.6	-0.9	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 5V, V_{GS}=0, f = 1KHz$	0.4	1.2		mS
Input Capacitance	C_{iss}	$V_{DS} = 5V, V_{GS}=0, f = 1MHz$		3.5	50	pF
Reverse Transfer Capacitance	C_{rss}			0.65	5	pF

■■ I_{DSS} Classification And Marking

Mark	K596A	K596B	K596C
Classification	A	B	C
I_{DSS}	100~170	150~240	210~350